PTSTDARD

Mono Silicon Wafer

Data Sheet

P-Type **166±0.25mm**

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Data Sheet

P-Type 166±0.25mm

Material Performance Parameters

Conductivity Type	P	P/N type tester
Doped element	Gallium	/
Crystallinity	Single crystal	Priority etching technology（FSTM F47-88）
Dislocation density/pcs/cm^2	≤500	Priority etching technology（FSTM F47-88）
Surface orientation	<100>±3°	X-ray diffractometer
Lateral crystal orientation	<010>, <001>±3°	X-ray diffractometer
Oxygen content (ppma)	≤16	FTIR (ASTM F121-83)
Carbon content (ppma)	≤1	FTIR (ASTM F123-91)
Lifetime (μs)	≥70	BCT-400
Resistivity (Ω.cm)	0.4-1.1	Silicon wafer automatic inspection equipment

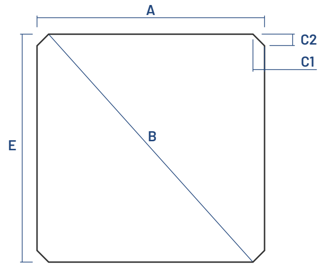
Geometric Rule Parameters

Chamfered edge shape	Round	/
Wafer margins (mm)	166±0.25mm	Silicon wafer automatic inspection equipment
Wafer diameter (mm)	ф223±0.25mm	Silicon wafer automatic inspection equipment
Arc length projection (mm)	8.55±0.5mm	Silicon wafer automatic inspection equipment
Perpendicularity	90±0.15°	Silicon wafer automatic inspection equipment
Thickness specification (μm)	130±10	Silicon wafer automatic inspection equipment
	135±10	Silicon wafer automatic inspection equipment

Appearance Quality

Surface quality	No visible pollution	Silicon wafer automatic inspection equipment
	No color difference, No bright lines	
Edge Chipping	Depth≤0.3mm , Length ≤0.5mm	Silicon wafer automatic inspection equipment
	Count ≤ 2/pcs, no V-shaped	
Saw mark (μm)	≤15	Silicon wafer automatic inspection equipment
Warpage/bending degree (μm)	≤40	Silicon wafer automatic inspection equipment
TTV (μm)	≤25	Silicon wafer automatic inspection equipment
Micro-crack/void	None	Silicon wafer automatic inspection equipment

Wafer dimensions



Size： 166±0.25mm

A： 166±0.25mm

E： 166±0.25mm

B： ϕ 223±0.25mm

C1： 8.55±0.5mm

C2： 8.55±0.5mm